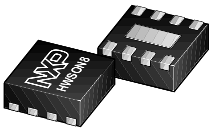


BGU8052

Low noise high linearity amplifier

Rev. 1 — 27 November 2013 | Product data sheet

1. Product profile

1.1 General description

The BGU8052 is a low noise high linearity amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 1.5 GHz and 2.5 GHz. It is housed in a 2 mm × 2 mm × 0.75 mm 8-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

1.2 Features and benefits

- Low noise performance: NF = 0.50 dB
- High linearity performance: $IP3_O$ = 36 dBm
- High input return loss > 15 dB
- High output return loss > 20 dB
- Unconditionally stable up to 20 GHz
- Programmable bias current (via resistor)
- Small 8-terminal leadless package 2 mm × 2 mm × 0.75 mm
- ESD protection on all terminals
- Moisture sensitivity level 1
- Fast shutdown to support TDD systems
- +5 V single supply

1.3 Applications

- Wireless infrastructure
- Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- General purpose wireless applications
- TDD or FDD systems
- Suitable for small cells

1.4 Quick reference data

Table 1. Quick reference data

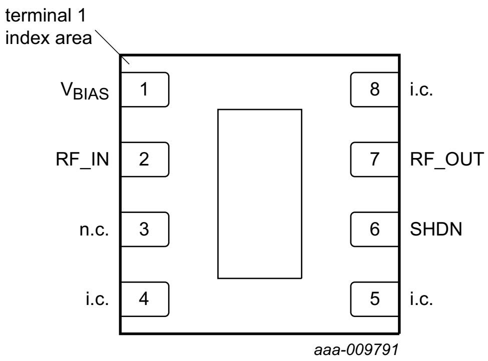
f = 1900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω; Rbias = 5.1 kΩ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 15 with components listed in Table 9 optimized for f = 1900 MHz.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CC}	supply current	on state		36	48	60	mA
		off state		-	2.8	-	mA
G_{ass}	associated gain	on state		17	18.5	20	dB
		off state		-	−23	-	dB
NF	noise figure		[1]	-	0.50	0.70	dB
$P_{L(1dB)}$	output power at 1 dB gain compression			-	18	-	dBm
$IP3_O$	output third-order intercept point	2-tone; tone spacing = 1 MHz; P_i = −15 dBm per tone		32	36	-	dBm

[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

2. Pinning information

2.1 Pinning



Transparent top view

Fig 1. Pin configuration

2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
V_{BIAS}	1	bias voltage
RF_IN	2	RF input
n.c.	3	not connected
i.c.	4, 5, 8	internally connected. Can be grounded or left open in the application.
SHDN	6	shutdown
RF_OUT	7	RF output
GND	exposed die pad	ground

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BGU8052	HWSON8	plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body 2 × 2 × 0.75 mm	SOT1327-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			-	6	V
$V_{ctrl(sd)}$	shutdown control voltage			-	2	V
I_{CC}	supply current			-	85	mA
$P_{i(RF)CW}$	continuous waveform RF input power			-	20	dBm
T_{stg}	storage temperature			–40	+150	°C
T_j	junction temperature			-	150	°C
P	power dissipation	$T_{case} \leq 125$ °C	[1]	-	510	mW
V_{ESD}	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001-2010		-	0.9	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B		-	2	kV

[1] Case is ground solder pad.

5. Recommended operating conditions

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		4.75	5	5.25	V
Z_0	characteristic impedance		-	50	-	Ω
T_{case}	case temperature		–40	-	+85	°C

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Typ	Unit
$R_{th(j-case)}$	thermal resistance from junction to case		[1][2]	50	K/W

[1] Case is ground solder pad.

[2] Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

7. Characteristics

Table 7. Characteristics

f = 1900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω; Rbias = 5.1 kΩ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 15 with components listed in Table 9 optimized for f = 1900 MHz.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CC}	supply current	on state		36	48	60	mA
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		off state		-	−23	-	dB
NF	noise figure		[1]	-	0.50	0.70	dB
$P_{L(1dB)}$	output power at 1 dB gain compression			-	18	-	dBm
$IP3_O$	output third-order intercept point	2-tone; tone spacing = 1 MHz; P_i = −15 dBm per tone		32	36	-	dBm
		2-tone; tone spacing = 1 MHz; P_i = −15 dBm per tone	[2]	30	34	-	dBm
RL_{in}	input return loss	on state		-	14.5	-	dB
		off state		-	8.4	-	dB
RL_{out}	output return loss			-	23	-	dB
ISL	isolation			-	23	-	dB
$t_{s(pon)}$	power-on settling time	P_i = −20 dBm; SHDN (pin 6) from HIGH to LOW	[2]	-	1.4	-	µs
$t_{s(poff)}$	power-off settling time	P_i = −20 dBm; SHDN (pin 6) from LOW to HIGH	[2]	-	0.4	-	µs
K	Rollett stability factor	both on state and off state up to f = 20 GHz		1	-	-	
$R_{pd(SHDN)}$	pull-down resistance on pin SHDN			-	20	-	kΩ

[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

[2] For TDD systems where fast switching is required, it is recommended to change C1 and C2 to 100 pF.

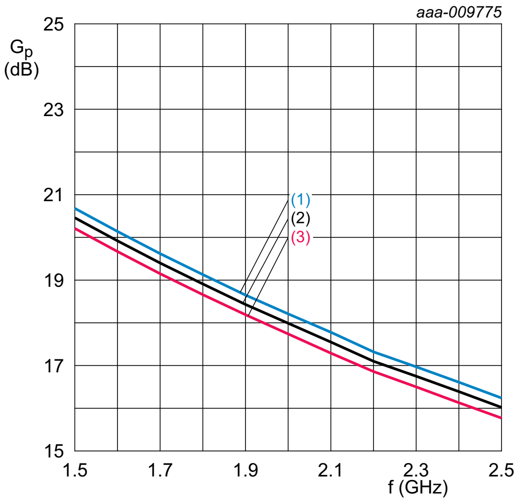
Table 8. Shutdown control

V_{CC} = 5 V; T_{amb} = 25 °C.

State	$V_{ctrl(sd)}$ [1] (V)
on state	≤ 0.6
off state	≥ 1.2

[1] Voltage on pin 6 (SHDN).

7.1 Graphs



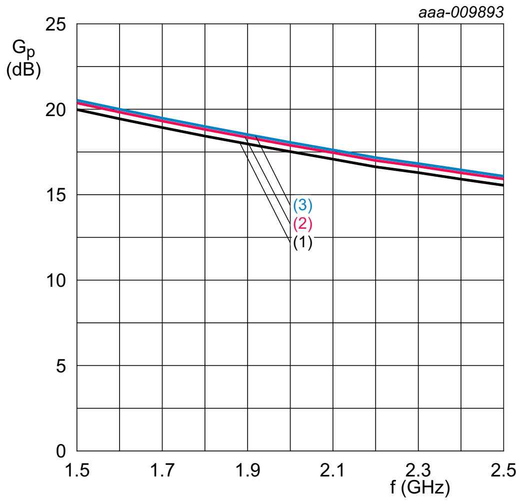
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = –40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 2. Power gain as a function of frequency; typical values



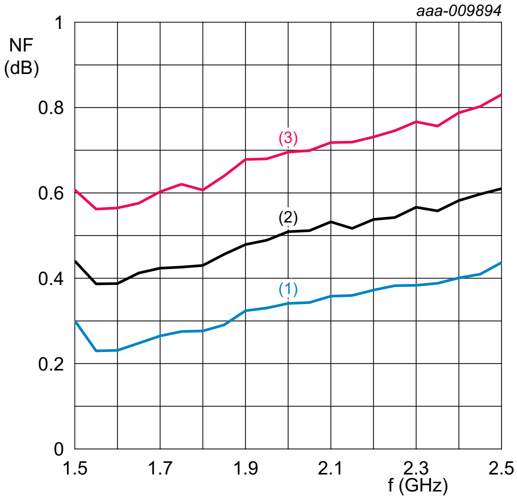
V_{CC} = 5 V; T_{amb} = 25 °C.

(1) I_{CC} = 30 mA

(2) I_{CC} = 45 mA

(3) I_{CC} = 60 mA

Fig 3. Power gain as a function of frequency; typical values



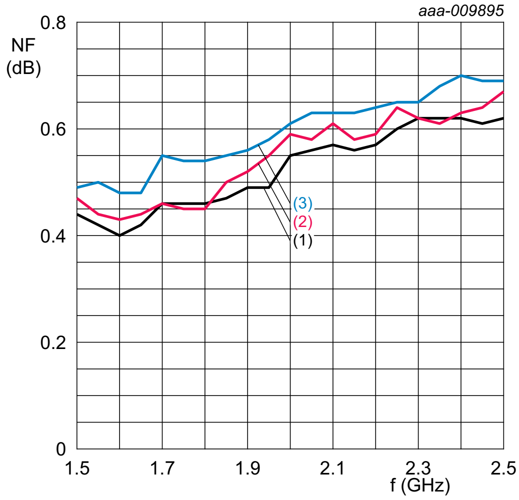
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = –40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 4. Noise figure as a function of frequency; typical values



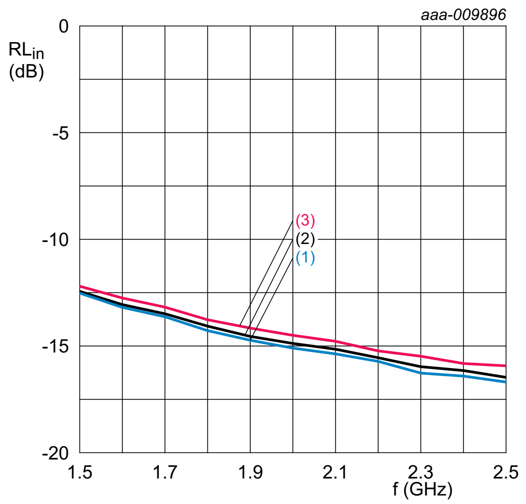
V_{CC} = 5 V; T_{amb} = 25 °C.

(1) I_{CC} = 30 mA

(2) I_{CC} = 45 mA

(3) I_{CC} = 60 mA

Fig 5. Noise figure as a function of frequency; typical values



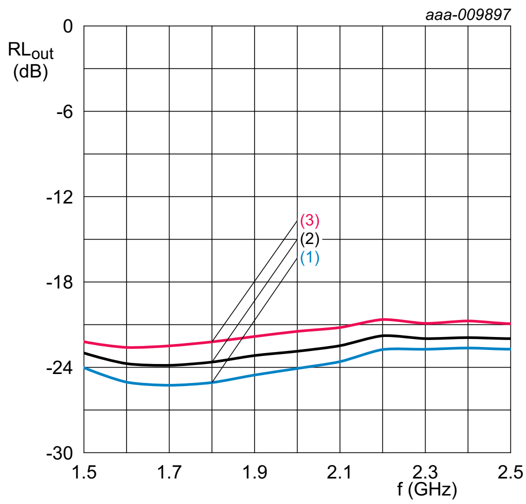
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = −40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 6. Input return loss as a function of frequency; typical values



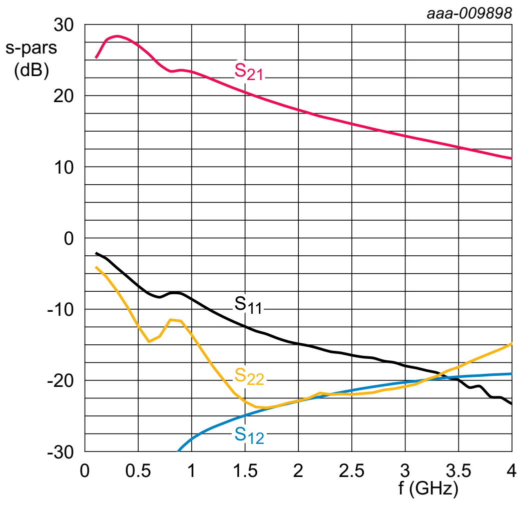
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = −40 °C

(2) T_{amb} = +25 °C

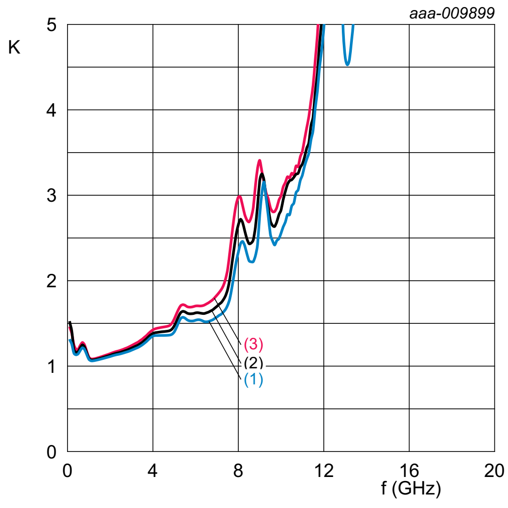
(3) T_{amb} = +85 °C

Fig 7. Output return loss as a function of frequency; typical values



V_{CC} = 5 V; T_{amb} = 25 °C; I_{CC} = 48 mA.

Fig 8. Wideband S-parameters as function of frequency; typical values



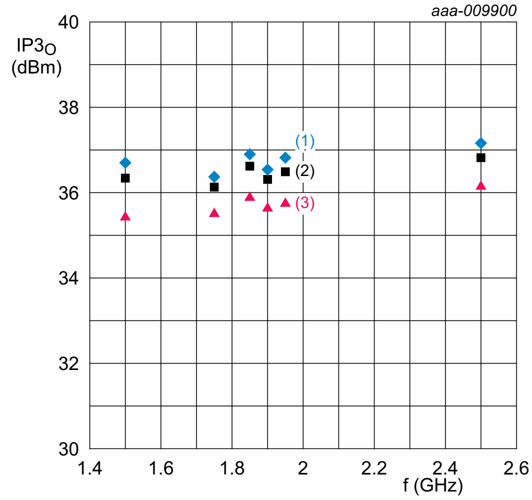
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = −40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 9. Rollet stability factor as a function of frequency; typical values



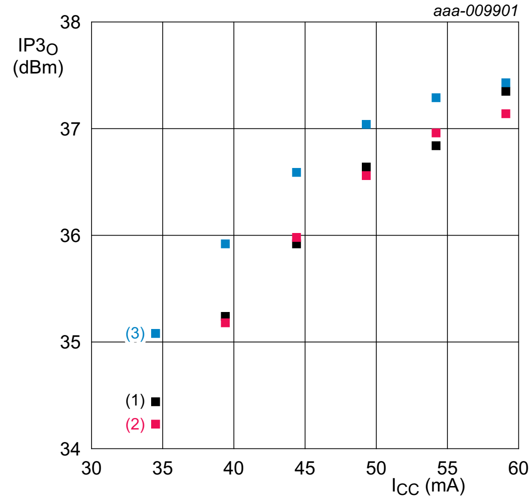
V_{CC} = 5 V; P_i = –15 dBm per tone; I_{CC} = 48 mA.

(1) T_{amb} = –40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 10. Output third-order intercept point as a function of frequency; typical values



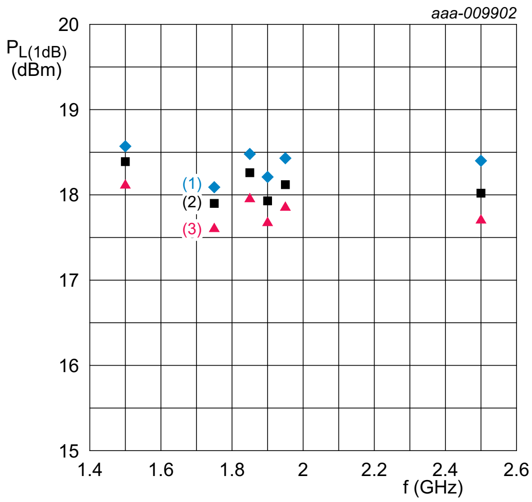
V_{CC} = 5 V; P_i = –15 dBm per tone; T_{amb} = 25 °C.

(1) f = 1500 MHz

(2) f = 1900 MHz

(3) f = 2500 MHz

Fig 11. Output third-order intercept point as a function of supply current; typical values



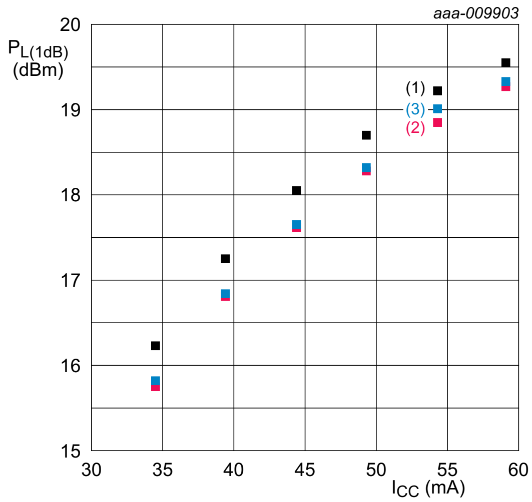
V_{CC} = 5 V; I_{CC} = 48 mA.

(1) T_{amb} = –40 °C

(2) T_{amb} = +25 °C

(3) T_{amb} = +85 °C

Fig 12. Output power at 1 dB gain compression as a function of frequency; typical values



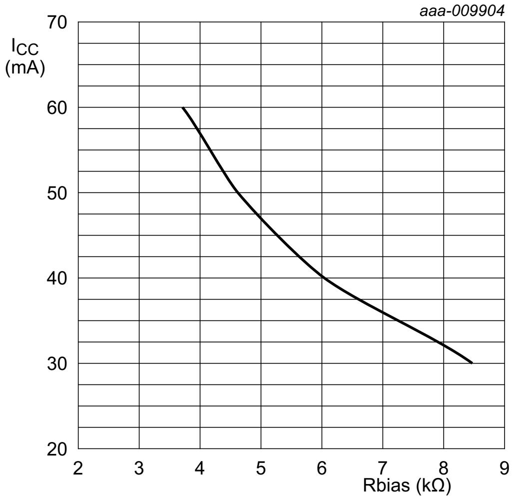
V_{CC} = 5 V; T_{amb} = 25 °C.

(1) f = 1500 MHz

(2) f = 1900 MHz

(3) f = 2500 MHz

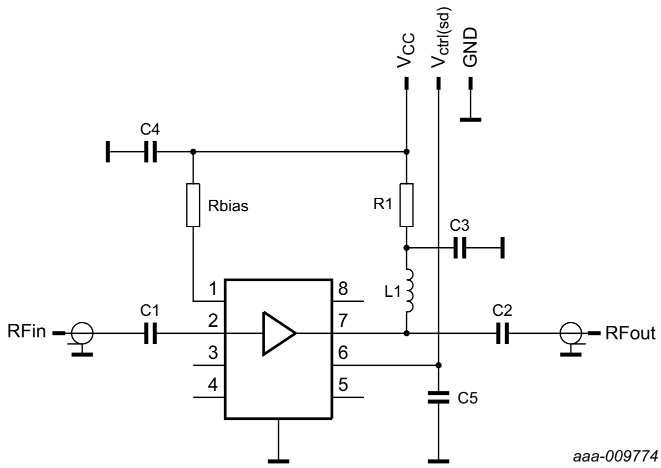
Fig 13. Output power at 1 dB gain compression as a function of supply current; typical values



V_{CC} = 5 V.

Fig 14. Supply current as a function of Rbias; typical values

8. Application information



See Table 9 for a list of components.

Fig 15. Schematic of application board

Table 9. List of components

See Figure 15 for schematics.

Component	Description	Value	Remarks
C1, C2	capacitor	100 nF	
		100 pF	recommended for TDD systems
C3	capacitor	10 pF	
C4	capacitor	5.6 nF	
C5	capacitor	10 pF	

Table 9. List of components *…continued*

See Figure 15 for schematics.

Component	Description	Value	Remarks
L1	inductor	15 nH	
R1	resistor	10 Ω	
Rbias	resistor	5.1 kΩ	

Table 10. Typical performance BGU8052 application board

All RF parameters are measured at the application board as shown in Figure 15 with the components as listed in Table 9 while optimized for: f = 1900 MHz; V_{CC} = 5 V; I_{CC} = 48 mA and T_{amb} = 25 °C.

Symbol	Parameter		f (MHz)							
			1500	1750	1850	1900	1950	2100	2300	2500
G_{ass}	associated gain		20.5	38.3	18.7	18.4	18.2	17.6	16.8	16.0
RL_{in}	input return loss		12.4	27.6	14.3	14.6	14.7	15.2	16.0	16.5
RL_{out}	output return loss		23.0	47.5	23.4	23.2	23.0	22.5	22.0	22.0
$P_{L(1dB)}$	output power at 1 dB gain compression		18.4	17.9	18.3	17.9	18.1	18.7	18.2	18.0
$IP3_O$	output third-order intercept point	[1]	36.3	36.1	36.6	36.3	36.5	36.5	35.2	36.8
		[1][2]	36.9	36.0	37.3	38.1	34.9	34.5	34.0	33.0
NF	noise figure	[3]	0.44	0.43	0.46	0.48	0.49	0.53	0.57	0.61

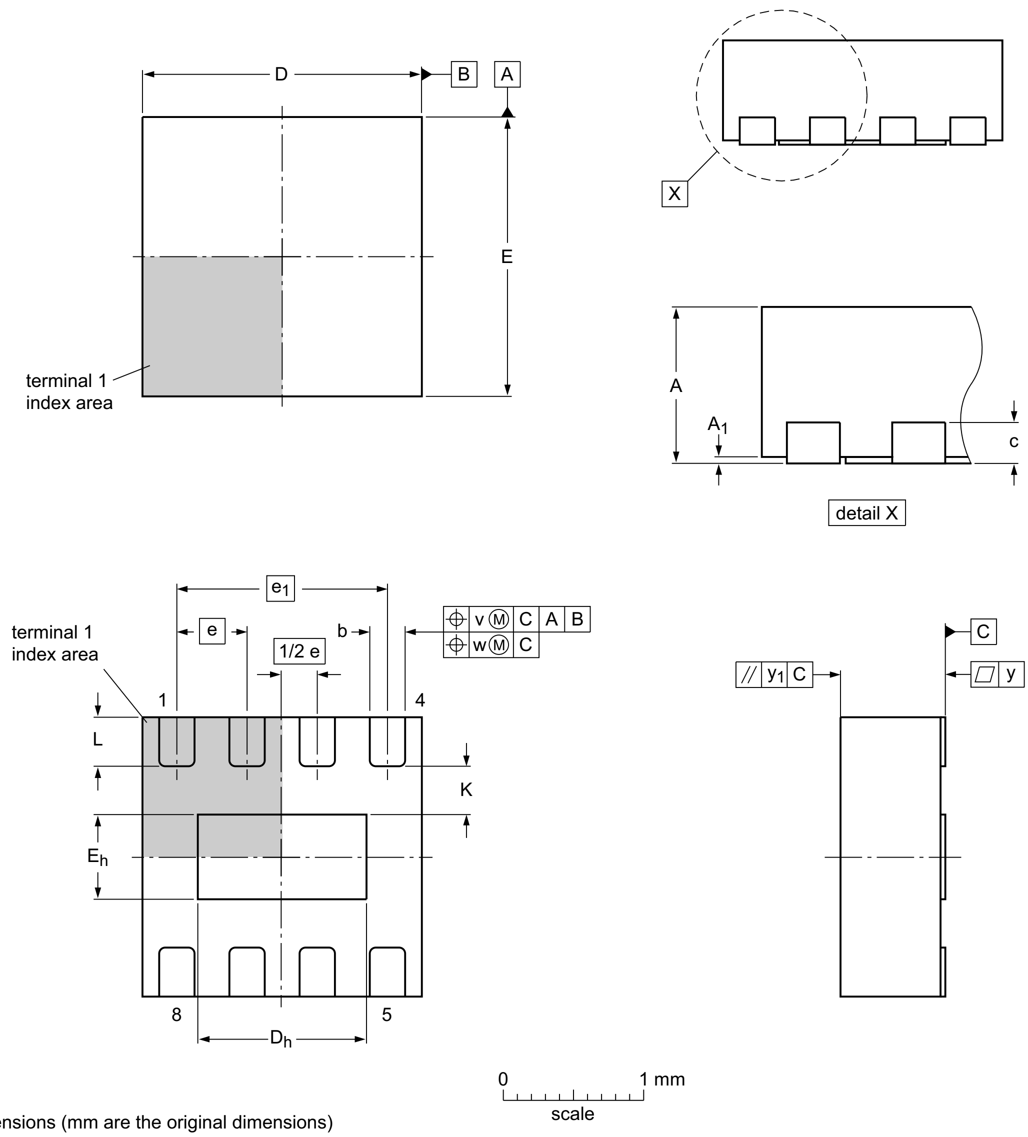
[1] 2-Tone; tone spacing = 1 MHz; P_i = −15 dBm per tone.

[2] For applications where fast switching is required, it is recommended to change C1 and C2 to 100 pF.

[3] Connector and board losses not de-embedded.

9. Package outline

HWSON8: plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body 2 x 2 x 0.75 mm **SOT1327-1**



Dimensions (mm are the original dimensions)

Unit		A	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	K	L	v	w	y	y_1
	max	0.80	0.05	0.30		2.05	1.25	2.05	0.65				0.40				
mm	nom	0.75	0.03	0.25	0.2	2.00	1.20	2.00	0.60	0.5	1.5		0.35	0.1	0.05	0.05	0.1
	min	0.70	0.00	0.20		1.95	1.15	1.95	0.55			0.35	0.30				

Note
1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot1327-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1327-1		MO-229				~~12-04-11~~ 12-04-15

Fig 16. Package outline SOT1327-1 (HWSON8)

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile Communication
LNA	Low Noise Amplifier
LTE	Long Term Evolution
RF	Radio Frequency
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8052 v.1	20131127	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term ‘short data sheet’ is explained in section “Definitions”.

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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13. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

14. Contents

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Document identifier: BGU8052